

# Single Line Bi-directional Transient Voltage Suppressor

#### **DESCRIPTION**

The SD4V5HHNC TVS diode is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebooks, and PDA's. It offers superior electrical characteristics such as low clamping voltage, low leakage current and high surge capability. It is designed to protect sensitive electronic components which are connected to power lines, from over-stress caused by ESD (Electrostatic Discharge), EFT (Electrical Fast Transients) and Lighting.

The SD4V5HHNC is in a DFN2020-3L package and will protect one bi-directional line. Standard products are Pb-free and Halogen-free.

## **FEATURES**

- ♦ Peak power dissipation: 4800W (8/20µs)
- ♦ Working voltages : 4.5V
- ♦Low leakage current
- ♦Low clamping voltage
- ♦Ultra-small package (2.0mm×2.0mm×0.5mm)
- ♦ Solid-state silicon-avalanche technology

## **MACHANICAL DATA**

- ♦DFN2020-3L package
- ♦Flammability Rating: UL 94V-0
- ♦ High temperature soldering guaranteed: 260°C/10s
- ♦ Packaging: Tape and Reel
- ♦Reel size: 7 inch

#### **ORDERING INFORMATION**

Device: SD4V5HHNCPackage: DFN2020-3LMarking: T45 008

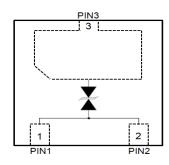
♦ Material: Halogen free and RoHS compliant

→ Packing: Tape & Reel→ Quantity per reel: 3,000pcs

# **APPLICATIONS**

- ♦Power supply protection
- ♦ Personal digital assistants (PDA's)
- ♦ Microprocessors based equipment
- ♦Power Management
- ♦ Cell phone Handsets and Accessories
- ♦ Portable Electronics
- ♦ Peripherals

## **PIN CONFIGURATION**



## **PACKAGE OUTLINE**

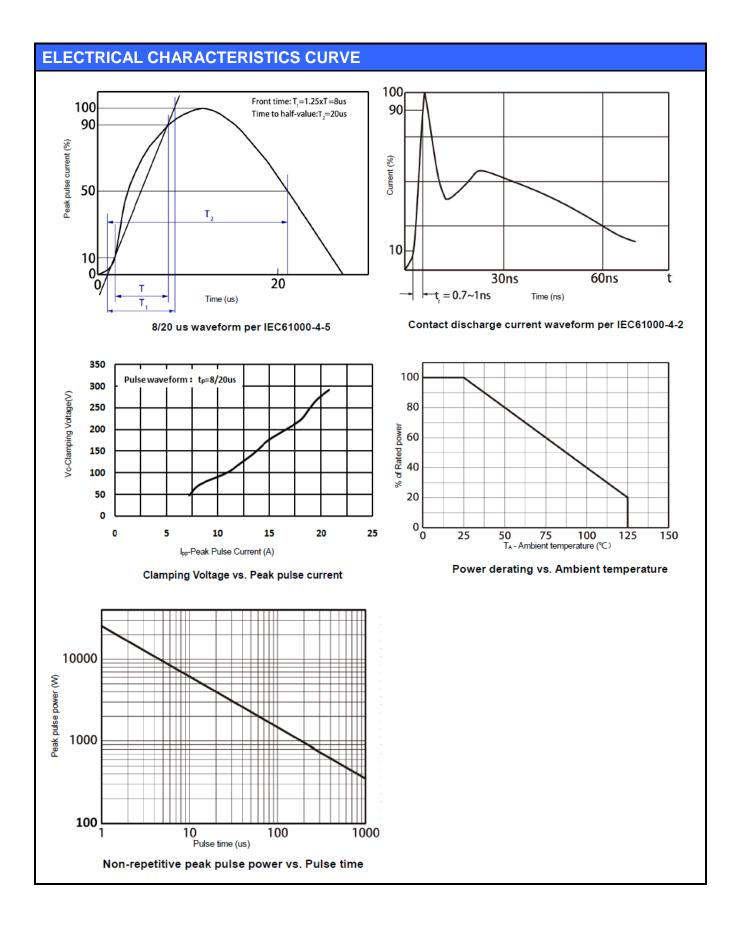




ABSOLUTE MAXIMUM RATING								
Symbol	Parameter	Value	Units					
V <sub>ESD</sub>	ESD per IEC 61000-4-2 (Contact) ESD per IEC 61000-4-2 (Air)	±30 ±30	kV					
P <sub>PP</sub>	Peak Pulse Power (8/20µs)	4800	W					
T <sub>OPT</sub>	T <sub>OPT</sub> Operating Temperature		°C					
T <sub>STG</sub>	T <sub>STG</sub> Storage Temperature		°C					
T <sub>L</sub>	Lead Soldering Temperature	260(10sec)	°C					

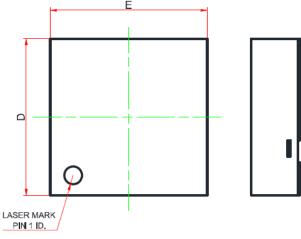
ELECTRICAL CHARACTERISTICS (Tamb=25°C)								
Symbol	Parameter	Test Condition	Min	Тур	Max	Units		
V <sub>RWM</sub>	Reverse Working Voltage				4.5	V		
$V_{BR}$	Reverse Breakdown Voltage	I <sub>T</sub> = 1mA	4.6	5.2	6.1	V		
I <sub>R</sub>	Reverse Leakage Current	$V_{RWM} = 4.5V$			1	uA		
I <sub>PP</sub>	Peak Pulse Current	t <sub>p</sub> = 8/20µs			240	А		
V <sub>C</sub>	Clamping Voltage	$I_{PP} = 150A, t_p = 8/20 \mu s$			16	V		
		$I_{PP} = 200A, t_p = 8/20 \mu s$			18	V		
		$I_{PP} = 240A$ , $t_p = 8/20\mu s$			20	V		
CJ	Junction Capacitance	$V_R = 0V$ , $f = 1MHz$	200	400	600	pF		

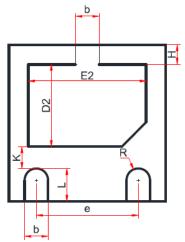


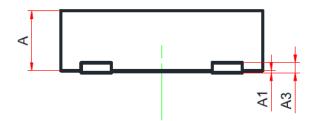




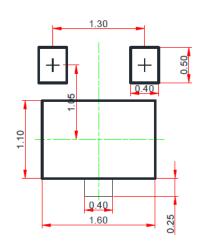








# Recommend Land Pattern (Unit: mm)



Symbol	Dimensions In Millimeters				
Gymbol	Min.	Тур.	Max.		
Α	0.51	0.55	0.60		
A1	0.00	0.02	0.05		
A3	0.15 REF.				
b	0.25	0.30	0.35		
D	1.90	2.00	2.10		
Е	1.90	2.00	2.10		
D2	0.85	1.00	1.10		
E2	1.35	1.50	1.60		
е	1.20	1.30	1.40		
Н	0.20	0.25	0.30		
K	0.20	0.30	0.40		
L	0.35	0.40	0.45		
R	0.15	-	-		

Note:

This recommended land pattern is for reference purpose only.